## 3D Si/C Particulate Nanocomposites Internally-Wired with Graphene Networks for High Energy and Stable Batteries

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## **Supporting Information**

Figure S1. SEM images of (a, b) Si/C-IWGN-1, (c, d) Si/C-IWGN-2, and TEM images of (e) SiNPs,(f) Si/C-1 and (g, h) Si/C-IWGN-1.



**Figure S2**. SEM images of (a, b) Si/C-1, (c, d) Si/C-2 and (e, f) Si/C-3.



Figure S3. TEM images of (a, b) Si/C-2 and (c, d) Si/C-3.



**Figure S4**. TGA profiles of reference Si/C samples, Si/C-IWGN-1, Si/C-IWGN-4 and Si/C-IWGN-5 run in air flow.



Figure S5. XRD patterns of (a) Si/C-1 and Si/C-IWGN-1 $\sim$ 3 and (b) Si/C-2 and Si/C-IWGN-4 $\sim$ 6 series samples.



**Figure S6**. (a) FTIR and (b) Raman spectra of GO, Si/C-IWGN-2(gel), thermally reduced rGO and Si/C-IWGN samples.



Figure S7. X-ray photoelectron spectra of SiNPs, Si/C-IWGN-3, Si/C-IWGN-4 and Si/C-IWGN-5.

Electrodes	Sheet resistance <sup>a</sup> (m $\Omega$ per square)	Coating thickness <sup>b</sup> (µm)	Resistivity <sup>c</sup> (Ω·cm)	Conductivity <sup>d</sup> (S·cm <sup>-1</sup> )
Si/C-1	1.97	40.3	7.9′10 <sup>-6</sup>	1.3′10 <sup>5</sup>
Si/C-IWGN-1	2.28	39.3	9.0´10 <sup>-6</sup>	1.1′10 <sup>5</sup>
Si/C-IWGN-2	38.15	36.2	1.4′10-4	7.1'10 <sup>3</sup>
Si/C-IWGN-3	56.52	36.0	2.0′10-4	5.0'10 <sup>3</sup>

 Table S1. Electrode sheet resistance and conductivity

Notes; *a*Sheet resistances are average values on  $10\sim12$  different measurements, *b*coating thicknesses are average values on 6 different measurements, *c*Resistivity = (sheet resistance) '(coating thickness) and *d*Conductivity = (Resistivity)<sup>-1</sup>.



Figure S8. Sheet resistivity and conductivity measured on electrodes of Si/C-1 and Si/C-IWGN-1~3 series samples.



Figure S9. SEM images of (a, b) Si/C-1 and (c, d) Si/C-IWGN-2 before (left column) and after cycling for 50 cycles at  $0.5A \text{ g}^{-1}$ .



**Figure S10**. SEM images of electrode cross-sections of graphite for its pristine and after the first lithiation and delithiation.

Samples	Si/C-IWGN-3	Si/C-IWGN-6	Si-Gr	Graphite
mg_ <sub>A.M.</sub> /cm <sup>2a</sup>	1.51	1.63	1.91	3.43
mg_total/cm <sup>2b</sup>	1.89	2.04	2.39	4.29
coating thickness (µm)°	31.0	37.2	22.1	26.3
coating density (g_ <sub>total</sub> /cm <sup>3</sup> ) <sup>b</sup>	0.61	0.55	1.09	1.63
specific capacity-1 (mAh/g_ <sub>A.M.</sub> ) <sup>a</sup>	994	1557	899	370
specific capacity-2 (mAh/g_total)	795	1246	719	296
volumetric capacity <sup>d</sup> (mAh/cm <sup>3</sup> total) <sup>b</sup>	484	682	777	483

 Table S2. Coating densities and volumetric capacities electrodes

Notes; <sup>a</sup>values based on the mass of active material (A.M.) only, <sup>b</sup>values based on the total mass inclusive of active material, binder and conductive additive coated on electrode, <sup>c</sup>measured by SEM of electrode cross-section, and <sup>d</sup>volumetric capacity ( $mAh/cm^3_{total}$ ) = specific capacity-2 ( $mAh/g_{total}$ ) × coating density ( $g_{total}/cm^3$ ).



**Figure S11**. Voltage profiles of graphite for the initial two cycles at the current of 100 mA  $g^{-1}$  between 0.005 – 2.0 V.